

Vortex lattice dynamics in a-NbGe detected by mode-locking experiments

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We observed mode-locking (ML) of rf-dc driven vortex arrays in a superconducting weak pinning a-NbGe film. The ML voltage shows the expected scaling $V \propto f\sqrt{B}$ with f the rf-frequency and B the magnetic field. For large dc-velocity (corresponding to a large ML frequency), the ML current step width exhibits a squared Bessel function dependence on the rf-amplitude as predicted for ML of a lattice moving elastically through a random potential.

I. INTRODUCTION

An important tool to study an interacting particle system moving over a (random) pinning potential, e.g. a sliding solid, charge density wave or vortex array, is to probe the force-velocity characteristics with a superimposed rf-drive. For a coherently (elastically) moving array, the rf-drive may interfere with lattice modes at an integer q times the 'washboard' frequency $f_w = v/a$, with a the periodicity of the array and v its velocity, when the frequency f of the rf-drive equals an integer fraction $1/p$ of qf_w [1,2]. In the particular case of a vortex array (VA), the resulting 'mode'-locking (ML) at the velocity $v_{p,q} = (p/q)fa$ appears as voltage 'plateaus' in the dc current-voltage (IV) curves (peaks in the differential conductance dI/dV). For a *plastically* moving VA, which may arise for strong random pinning, at small velocity or in the vortex liquid phase, the coherent modes are destroyed and the ML effect vanishes [3]. This distinction allows to construct dynamic phase diagrams from the velocity or magnetic field dependence of ML, as we have shown recently for confined VA's in disordered channels [4].

Focussing on a disordered film with an elastically moving VA (at relatively large velocity), Ref. [1] predicts a particular form for the dc-current range ΔI over which the ML effect occurs. To first approximation, the current range $\Delta I_{1,1}$ of the main ML step ($p = q = 1$) is:

$$\Delta I_{1,1} = 2I_c [J_1(I_{rf}R_f/V_{1,1})]^2, \quad (1)$$

where $J_1(x)$ is the first order Bessel function, R_f the flux flow resistance, $V_{1,1}$ the fundamental ML voltage and I_c the dc-critical current in absence of rf-drive.

So far, the only report of ML of a VA in a disordered superconducting film is Ref. [2], where Al films were used and the rf-amplitude dependence was not addressed. In this report we show that a-NbGe films with weak random pinning [5,6] also exhibit the ML effect and we examine its dependence on I_{rf} .

II. EXPERIMENTAL

A 400 nm thick amorphous (a-)NbGe strip ($T_c \simeq 3.0$ K and normal state resistivity $\rho_n \simeq 2 \mu\Omega\text{m}$), with current leads covered by a strong pinning NbN film ($T_c \simeq 10$ K) to reduce sample impedance, was prepared by RF sputtering and standard lithography. In the resulting four-probe configuration both the strip width and the distance between voltage contacts was 100 μm . In the transport measurement, the rf-current (amplitude ranging from 0 – 0.5 mA) was applied through a matched circuit. All data were taken with the sample immersed in superfluid ^4He at a temperature $T = 1.8$ K and the magnetic field B perpendicular to the film.

III. RESULTS AND DISCUSSION

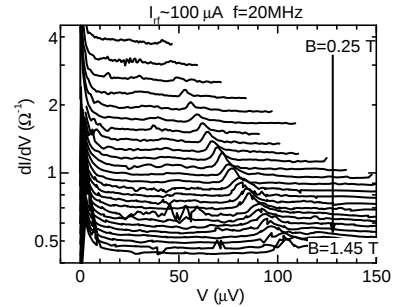


FIG. 1. Differential conductance dI/dV versus dc-voltage V in presence of a 20 MHz rf-current of amplitude $I_{rf} \simeq 100 \mu\text{A}$ for fields ranging from $B = 0.25$ T to 1.45 T with steps of 50 mT.

In Fig. 1 we plot dI/dV versus the dc-voltage measured with a superimposed rf-current of 20 MHz and an amplitude $I_{rf} \simeq 100 \mu\text{A}$ at magnetic fields B ranging from 0.25 to 1.45 T. In the whole field range, the curves show a clear ML peak in dI/dV which can be identified as the fundamental $p = q = 1$. Additionally, for some fields, (weaker) subharmonic peaks can be observed. The ML voltage $V_{1,1}$ of the main peak scales with magnetic field as $V \sim \sqrt{B}$, in agreement with the relation $V \propto v \cdot B = faB$

where $a \sim 1/\sqrt{B}$. In addition we checked that the ML voltage at fixed field scales linearly with the frequency of the applied rf-current. The observed ML implies that the moving VA predominantly experiences elastic deformations, validating the previous use of the collective pinning theory in this material [5].

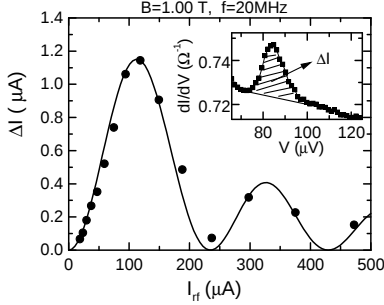


FIG. 2. Data points: ML current width of the fundamental step $\Delta I_{1,1}$ (as defined in the inset) versus I_{rf} at $B = 1.00$ T and $f = 20$ MHz. The drawn line represents Eq. (1) with $I_c = 1.7 \mu\text{A}$ as the only fit parameter.

We now turn to the rf-amplitude dependence of the ML. Due to rounding of the steps in the IV curves the ML current width ΔI is best defined as shown in the inset to Fig. 2. The data in the main panel show the result of such analysis at $B = 1$ T. The width ΔI clearly exhibits oscillatory behavior as function of I_{rf} . We also plot the dependence according to Eq. (1) (drawn line) where both R_f and $V_{1,1}$ were extracted from the experiment, the only fit parameter being I_c . The experimental data follow the theoretical prediction remarkably well. The fitted value $I_c = 1.7 \mu\text{A}$ is smaller than the critical current $I_{c,L} \simeq 6 \mu\text{A}$ determined by linearly extrapolating the 'bare' IV curve (at $I_{rf} = 0$) to $V = 0$. This difference may arise from the approximation made in Eq. (1) (see [1]). Comparing our result to the numerical work of Kolton *et al.* [3], we find no evidence for their sugges-

tion that $\Delta I \sim J_1(I_{rf}R_f/V_{1,1})$, valid for an rf-dc driven Josephson junction at large voltage (a single particle moving rapidly in a periodic potential). This discrepancy with their results, including the lack of step broadening, might originate from the neglect of long wavelength fluctuations in a finite size simulation.

Finally we mention that preliminary data taken at a larger frequency $f = 100$ MHz exhibit ML up to a field $B^* (< B_{c2})$ at which the critical current has completely vanished and the IV curves have become fully linear with a slope $R_f \simeq 0.75R_n$. The field B^* may be identified as the equilibrium melting field of the 2D vortex lattice, in line with Ref. [6]. For fields slightly below B^* , ML sensitively depends on the frequency. Since the VA softens considerably just below melting, the effect of pinning disorder is stronger in this regime. Based on the dynamic ordering theory in [7] and our measurements in disordered mesoscopic channels [4], one then indeed expects the appearance of a coherent state to depend strongly on the vortex velocity.

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